

Bridge Rectifier

SK 55 D

Target Data

Features

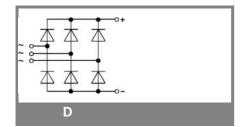
- · Compact design
- One screw mounting
- Heat transfer and insulation through direct copper bonded aluminium oxide ceramic (DCB
- Up to 1600V reverse voltage
- High surge currents
- Glass passived diodes chips
- UL recognized, file no. E 63 532

Typical Applications

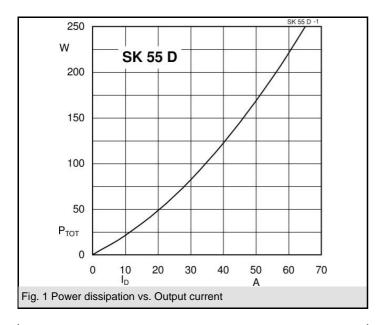
- Input rectifier for power supplies
- Rectifier

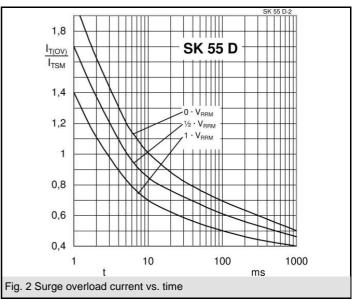
V _{RSM}	V_{RRM}, V_{DRM}	I _D = 55 A (full conduction)
V	V	(T _s = 80 °C)
800	800	SK 55 D 08
1200	1200	SK 55 D 12
1600	1600	SK 55 D 16

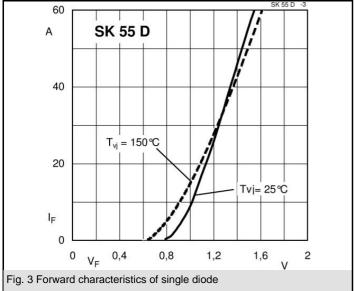
Symbol	Conditions	Values	Units
I_D	T _s = 80 °C	55	Α
I_D	T _s = 100 °C	45	Α
I _{FSM}	T _{vj} = 25 °C; 10 ms	370	A
	T _{vj} = 150 °C; 10 ms	270	Α
i²t	T _{vj} = 25 °C; 8,310 ms	685	A²s
	T _{vj} = 150 °C; 8,310 ms	365	A²s
V _F	T _{vi} = 25 °C; I _F = 25 A	max. 1,25	V
V _(TO)	T _{vi} = 150 °C	max. 0,8	V
r _T	T _{vi} = 150 °C	max. 13	mΩ
I_{RD}	T_{vj} = 150 °C; V_{DD} = V_{DRM} ; V_{RD} = V_{RRM}	max. 4	mA
			mA
$R_{th(j-s)}$	per diode	2,15	K/W
	per module	0,36	K/W
Т	terminals, 10s	260	°C
T _{solder} T _{vi}	lommais, res	-40+150	°C
T _{stg}		-40+125	°C
V _{isol}	a. c. 50 Hz; r.m.s.; 1 s / 1 min.	3000 (2500)	V
M _s	mounting torque to heatsink	2	Nm
M_t			
m	approx. weight	19	g
Case	SEMITOP® 2	T 7	



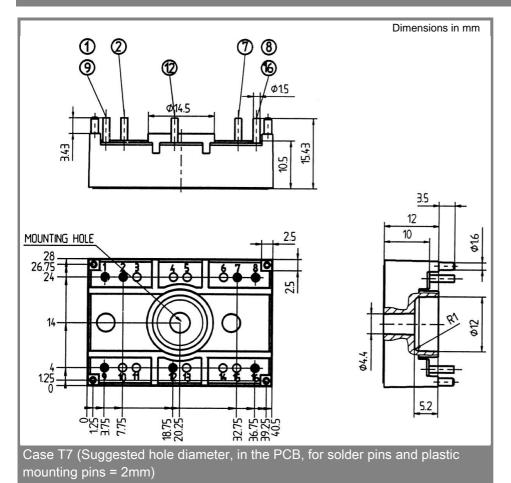
SK 55 D

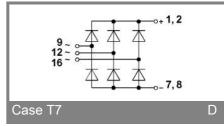






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